

4859597
345/206, 98, 100

Application No. 08/818,884
Attorney Docket No. 0756-1748

a driving circuit including at least another one thin film transistor for driving the active matrix circuit formed over said first surface of the insulating substrate;

CPT
SI
a counter substrate facing the first surface of said insulating substrate with a [liquid crystal material disposed] gap therebetween, said counter substrate covering said active matrix circuit and said driving circuit wherein said insulating substrate extends beyond at least one side edge of the counter substrate so as to provide an extended portion; and

at least one semiconductor integrated circuit chip disposed over said first surface of the extended portion of the insulating substrate and operationally connected with the driving circuit,

wherein said at least one thin film transistor and said at least another one thin film transistor are formed from a common semiconductor film formed over the first surface of the insulating substrate.

7. (Amended) A [liquid crystal] display device comprising:

a substrate having a first surface;

an active matrix circuit including at least one thin film transistor formed over the first surface of the substrate;

a driving circuit including at least another one thin film transistor for driving the active matrix circuit formed over the first surface of the substrate; and

at least one semiconductor integrated circuit chip disposed over the first surface of the substrate and operationally connected to said driving circuit wherein said semiconductor integrated circuit chip is at least one of a memory, an input port, a memory and a CPU,

Cont'd
52
wherein said at least one thin film transistor and said at least another one thin film transistor are formed from a common semiconductor film formed over the first surface of the substrate, and

wherein said at least one thin film transistor of the active matrix circuit has at least one lightly doped drain between a channel region and a drain region thereof.

53 124
9. (Amended) The device of claim 7 wherein [the semiconductor integrated circuit chip comprises a central processing unit] said memory is a correction memory.

10. (Amended) The device of claim 7 [wherein the semiconductor integrated circuit chip comprises a memory] further comprising a liquid crystal adjacent to said active matrix circuit.

54 Sub K3
17. (Amended) An electric device comprising:
a substrate having an insulating surface;
a plurality of thin film transistors formed on the insulating surface, said plurality of thin film transistors being formed from a common semiconductor film formed on said insulating surface; and
at least one single crystalline semiconductor integrated circuit chip formed on the insulating surface wherein said semiconductor integrated circuit chip is at least one of a memory, an input port, a memory and a CPU;

wherein at least one of the thin film transistors is provided as an active matrix circuit,
at least another one of the thin film transistors is provided as at least one driving circuit for driving
the active matrix circuit and the semiconductor integrated circuit chip is provided as a control circuit
for controlling the driving circuit, and wherein said common semiconductor film is formed by
crystallizing a semiconductor film comprising [amorphous] amorphous silicon deposited on said
insulating surface.

21. (Amended) An electric device comprising:

a first substrate;
an active matrix circuit formed over said first substrate with at least one thin film
transistor;
a driving circuit formed over said first substrate with at least one other thin film
transistor for driving the active matrix circuit;
a second substrate facing said first substrate with a gap therebetween, said first
substrate extending beyond at least one side edge of the second substrate to provide an extended
portion wherein said second substrate covers said active matrix circuit and said driving circuit; and
a semiconductor integrated circuit chip disposed over the extended portion of said
first substrate and operationally connected to said driving circuit,
wherein said at least one thin film transistor and said one other thin film transistor are
formed from a common semiconductor film obtained by crystallizing a semiconductor film
comprising amorphous silicon deposited over said first substrate.

32. (Amended) A [liquid crystal] display device comprising:

a first substrate having an insulating surface;

an active matrix circuit including a first plurality of thin film transistors formed on
the insulating surface of the first substrate;

a driving circuit including a second plurality of thin film transistors formed over the
insulating surface of the first substrate for driving said active matrix circuit;

a second substrate facing said first substrate with a liquid crystal material interposed
therebetween, said first substrate having an extended portion which extends beyond at least one side
edge of the second substrate wherein said second substrate covers said active matrix circuit and said
driving circuit;

at least one semiconductor integrated circuit chip disposed over the extended portion
of the first substrate and operationally connected to said driving circuit,

wherein said first and second plurality of thin film transistors are formed from a
common semiconductor film formed over said first substrate, and each of said first plurality of thin
film transistors has at least one lightly doped drain between a channel region and a drain region
thereof.

36. (Amended) A [liquid crystal] display device comprising:

a first substrate having an insulating surface;

an active matrix circuit including a first plurality of thin film transistors formed on
the insulating surface of the first substrate;

a driving circuit including a second plurality of thin film transistors formed over the insulating surface of the first substrate for driving said active matrix circuit;

a second substrate facing said first substrate with a [liquid crystal material interposed] gap therebetween, said first substrate having an extended portion which extends beyond at least one side edge of the second substrate wherein said second substrate covers said active matrix circuit and said driving circuit;

at least one semiconductor integrated circuit chip disposed over the extended portion of the first substrate and operationally connected to said driving circuit,

wherein each of said first plurality of thin film transistors is a bottom gate type transistor in which a gate electrode is located below a channel region of the transistor, and each of said second plurality of thin film transistors is a top gate type transistor in which a gate electrode is located over a channel region of the transistor.

38. (Amended) A [liquid crystal] display device comprising:

a first substrate having an insulating surface;

an active matrix circuit including a first plurality of thin film transistors formed on the insulating surface of the first substrate;

a driving circuit including a second plurality of thin film transistors formed over the insulating surface of the first substrate for driving said active matrix circuit;

58 Cnt'l
a second substrate facing said first substrate with a [liquid crystal material interposed]
gap therebetween, said first substrate having an extended portion which extends beyond at least one
side edge of the second substrate;

at least one semiconductor integrated circuit chip disposed over the extended portion
of the first substrate and operationally connected to said driving circuit,

wherein said semiconductor integrated circuit chip is selected from the group
consisting of a correction memory, a memory, a CPU, and an input port.

Please add new claims 40-50 as follows:

--40. The device according to claim 1 further comprising a liquid crystal material disposed
between said insulating substrate and said counter substrate.

59 sub K6
41. The device according to claim 38 further comprising a liquid crystal material disposed
between said first and second substrates.

42. The device according to claim 36 further comprising a liquid crystal material disposed
between said first and second substrates.

→ 43. The device according to claim 38 further comprising a liquid crystal material disposed
between said first and second substrates.

44. the electric device according to claim 1 wherein said semiconductor integrated circuit chip is connected to a wiring comprising indium tin oxide formed over said insulating substrate.

45. The device according to claim 7 wherein said semiconductor integrated circuit chip is connected to a wiring comprising indium tin oxide formed over said substrate.

cont'd
59
28
91
46. The device according to claim 17 wherein said semiconductor integrated circuit chip is connected to a wiring comprising indium tin oxide formed over said substrate.

47. The device according to claim 21 wherein said semiconductor integrated circuit chip is connected to a wiring comprising indium tin oxide formed over said first substrate.

48. The device according to claim 32 wherein said semiconductor integrated circuit chip is connected to a wiring comprising indium tin oxide formed over said first substrate.

49. The device according to claim 36 wherein said semiconductor integrated circuit chip is connected to a wiring comprising indium tin oxide formed over said first substrate.

50. The device according to claim 38 wherein said semiconductor integrated circuit chip is connected to a wiring comprising indium tin oxide formed over said first substrate.--
